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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/553,416	10/17/2005	Tadahiro Ohmi	039262-0143	1517
	7590 10/28/200 LARDNER LLP	EXAMINER		
SUITE 500	T NIXI	TRAN, THIEN F		
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			2895	
		MAIL DATE	DELIVERY MODE	
			10/28/2008	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary		Applica	tion No.	Applicant(s)		
		10/553,	416	OHMI ET AL.		
		Examin	er	Art Unit		
		Thien F.	Tran	2895		
- Period fo	- The MAILING DATE of this commun Reply	ication appears on t	he cover sheet with the	correspondence a	ddress	
A SHC WHICI - Extens after S - If NO - Failure Any re	DRTENED STATUTORY PERIOD FOR HEVER IS LONGER, FROM THE MISSIONS OF time may be available under the provisions SIX (6) MONTHS from the mailing date of this commoveriod for reply is specified above, the maximum state to reply within the set or extended period for reply ply received by the Office later than three months and patent term adjustment. See 37 CFR 1.704(b).	AILING DATE OF of 37 CFR 1.136(a). In no nunication. atutory period will apply and will, by statute, cause the a	FHIS COMMUNICATIO event, however, may a reply be ti will expire SIX (6) MONTHS fror pplication to become ABANDON	N. mely filed n the mailing date of this ED (35 U.S.C. § 133).		
Status						
2a)⊠ 3)□ :	Responsive to communication(s) file This action is FINAL . Since this application is in condition closed in accordance with the practic	2b)∏ This action is for allowance exce _l	ot for formal matters, pr		e merits is	
Dispositio	on of Claims					
5)	Claim(s) 1-24 is/are pending in the acta) Of the above claim(s) 13-24 is/are Claim(s) is/are allowed. Claim(s) 1-12 is/are rejected. Claim(s) is/are objected to. Claim(s) are subject to restrict on Papers The specification is objected to by the drawing(s) filed on is/are: Applicant may not request that any objected to above the drawing of t	e withdrawn from one tion and/or election election election election election and election election election election and election electi	requirement. b)⊡ objected to by the			
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d). 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
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Priority under 35 U.S.C. § 119 12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some color None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No. 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.						
2) Notice 3) Inform	of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (Pation Disclosure Statement(s) (PTO/SB/08) No(s)/Mail Date 10/17/05, 11/15/05.	TO-948)	4) Interview Summar Paper No(s)/Mail D 5) Notice of Informal 6) Other:)ate		

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Fujii et al (US 5,170,231) in view of Ohmi (US 6,677,648).

Fujii et al disclose a semiconductor device (Fig. 3A) characterized by comprising a semiconductor substrate 30 made of SiC; and an insulating film 33 of thermal oxide formed on the semiconductor substrate. Fujii et al does not disclose the insulating film 33 containing a rare gas at least partly. Ohmi discloses forming silicon oxide films having, even though at low temperature plasma oxidation, characteristics and reliability superior to those of silicon thermal oxide films formed at a high temperature. The silicon oxide films containing krypton (a rare gas). It would have been obvious to a person having ordinary skill in the art at the time the invention was made to substitute the thermal silicon oxide of the gate insulating film 33 with the silicon oxide film containing krypton as taught by Ohmi in order to realize a high quality silicon oxide film superior to a conventional thermal oxide film so that a high performance transistor integrated circuit can be realized, such as an improvement of reliability of element isolation and an improvement of drive performance of a MOS transistor (see col. 3, lines 58-62, and col. 4, lines 4-7). The claim limitations "formed by a plasma treatment" are taken to be

product by process limitations. A product by process claim directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See In re Fessman, 180 USPQ 324, 326 (CCPA 1974); In re Marosi et al., 218 USPQ 289, 292 (Fed. Cir. 1983); and particularly In re Thorpe, 227 USPQ 964, 966 (Fed. Cir. 1985), all of which make it clear that it is the patentability of the final structure of the product "gleaned" from the process steps, which must be determined in a "product by process" claim, and not the patentability of the process. See also MPEP 2113. Moreover, an old and obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Regarding claim 2, the insulating film includes a gate insulating film.

Regarding claim 3, the insulating film contains at least one of krypton (Kr), argon (Ar), and xenon (Xe) as the rare gas.

Regarding claim 4, at least part of said insulating film is one of an oxide film, an oxynitride film, and a nitride film.

Regarding claim 5, the SiC forming the semiconductor substrate 30 is a single crystal.

Regarding claim 6, the claim limitations "formed by plasma treatment where a temperature of the substrate is 600°C or less" are taken to be product by process limitations. A product by process claim directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See In re Fessman, 180 USPQ 324, 326 (CCPA 1974); In re Marosi et al., 218 USPQ 289, 292 (Fed. Cir. 1983); and particularly In re Thorpe, 227 USPQ 964, 966 (Fed. Cir. 1985), all of which make it

clear that it is the patentability of the final structure of the product "gleaned" from the process steps, which must be determined in a "product by process" claim, and not the patentability of the process. See also MPEP 2113. Moreover, an old and obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Regarding claim 7, the claim limitations "formed by one of direct oxidation, direct nitriding, and direct oxynitriding of a microwave-excited plasma" are taken to be product by process limitations. A product by process claim directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See In re Fessman, 180 USPQ 324, 326 (CCPA 1974); In re Marosi et al., 218 USPQ 289, 292 (Fed. Cir. 1983); and particularly In re Thorpe, 227 USPQ 964, 966 (Fed. Cir. 1985), all of which make it clear that it is the patentability of the final structure of the product "gleaned" from the process steps, which must be determined in a "product by process" claim, and not the patentability of the process. See also MPEP 2113. Moreover, an old and obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Regarding claim 8, the insulating film includes at least one of an oxide film, a nitride film, and an oxynitride film. The claim limitations "formed by microwave-excited plasma CVD" are taken to be product by process limitations. A product by process claim directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See In re Fessman, 180 USPQ 324, 326 (CCPA 1974); In re Marosi et al., 218 USPQ 289, 292 (Fed. Cir. 1983); and particularly In re Thorpe, 227 USPQ

964, 966 (Fed. Cir. 1985), all of which make it clear that it is the patentability of the final structure of the product "gleaned" from the process steps, which must be determined in a "product by process" claim, and not the patentability of the process. See also MPEP 2113. Moreover, an old and obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Regarding claim 9, the insulating film includes at least one of an oxide film, a nitride film, and an oxynitride film. The claim limitations "formed by one of direct oxidation, direct nitriding, and direct oxynitriding of a microwave-excited plasma and then by microwave-excited plasma CVD" are taken to be product by process limitations. A product by process claim directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See In re Fessman, 180 USPQ 324, 326 (CCPA 1974); In re Marosi et al., 218 USPQ 289, 292 (Fed. Cir. 1983); and particularly In re Thorpe, 227 USPQ 964, 966 (Fed. Cir. 1985), all of which make it clear that it is the patentability of the final structure of the product "gleaned" from the process steps, which must be determined in a "product by process" claim, and not the patentability of the process. See also MPEP 2113. Moreover, an old and obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Regarding claim 10, Fuji et al. in view of Ohmi as described above discloses all elements as claimed. The claim limitations "formed by a plasma treatment" and "formed by one of direct oxidation, direct nitriding, and direct oxynitriding of a microwave-excited plasma under a condition where a temperature of the substrate is 600°C or less" are

taken to be product by process limitations. A product by process claim directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See In re Fessman, 180 USPQ 324, 326 (CCPA 1974); In re Marosi et al., 218 USPQ 289, 292 (Fed. Cir. 1983); and particularly In re Thorpe, 227 USPQ 964, 966 (Fed. Cir. 1985), all of which make it clear that it is the patentability of the final structure of the product "gleaned" from the process steps, which must be determined in a "product by process" claim, and not the patentability of the process. See also MPEP 2113. Moreover, an old and obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Regarding claim 11, Fujii et al. in view of Ohmi as described above discloses all elements as claimed. The claim limitations "formed by a plasma treatment" and "formed by one of oxidation, nitriding, and oxynitriding by microwave-excited plasma CVD under a condition where a temperature of the substrate is 600°C or less" are taken to be product by process limitations. A product by process claim directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See In re Fessman, 180 USPQ 324, 326 (CCPA 1974); In re Marosi et al., 218 USPQ 289, 292 (Fed. Cir. 1983); and particularly In re Thorpe, 227 USPQ 964, 966 (Fed. Cir. 1985), all of which make it clear that it is the patentability of the final structure of the product "gleaned" from the process steps, which must be determined in a "product by process" claim, and not the patentability of the process. See also MPEP 2113. Moreover, an old and obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Regarding claim 12, Fujii et al. in view of Ohmi as described above discloses all elements as claimed. The claim limitations "formed by a plasma treatment" and "is formed, under a condition where a temperature of the substrate is 600° C or less, by one of direct oxidation, direct nitriding, and direct oxynitriding of a microwave-excited plasma and then by one of oxidation, nitriding, and oxynitriding by microwave-excited plasma CVD" are taken to be product by process limitations. A product by process claim directed to the product per se, no matter how actually made, In re Hirao, 190 USPQ 15 at 17 (footnote 3). See In re Fessman, 180 USPQ 324, 326 (CCPA 1974); In re Marosi et al., 218 USPQ 289, 292 (Fed. Cir. 1983); and particularly In re Thorpe, 227 USPQ 964, 966 (Fed. Cir. 1985), all of which make it clear that it is the patentability of the final structure of the product "gleaned" from the process steps, which must be determined in a "product by process" claim, and not the patentability of the process. See also MPEP 2113. Moreover, an old and obvious product produced by a new method is not a patentable product, whether claimed in "product by process" claims or not.

Response to Arguments

Applicant's arguments filed 07/17/2008 have been fully considered but they are not persuasive. Applicant contends that Fujii and Ohmi do not teach the combination of features of an insulating film formed by a plasma treatment and containing a rare gas on a SiC substrate or the benefits in suppression of an increase in interface states as described in the specification. The examiner respectfully disagrees with the remark because it is clear as explained above that Fujii in view of Ohmi disclose the same structure as claimed, an insulating film containing a rare gas on a SiC substrate. Also,

"a plasma treatment" is taken to be process limitations that cannot impart patentability to a product claim where the product is not patentably distinguished over the prior art. In re Dike, 394 F.2d 584, 157 USPQ 581 (CCPA 1968). It is noted that Ohmi also discloses the insulating film formed by a plasma treatment and containing a rare gas as claimed.

In response to applicant's argument that the references fail to show certain features of applicant's invention, it is noted that the features upon which applicant relies (i.e., suppression of an increase in interface states) are not recited in the rejected claim(s). Although the claims are interpreted in light of the specification, limitations from the specification are not read into the claims. See *In re Van Geuns*, 988 F.2d 1181, 26 USPQ2d 1057 (Fed. Cir. 1993).

In response to applicant's arguments against the references individually, one cannot show nonobviousness by attacking references individually where the rejections are based on combinations of references. See *In re Keller*, 642 F.2d 413, 208 USPQ 871 (CCPA 1981); *In re Merck & Co.*, 800 F.2d 1091, 231 USPQ 375 (Fed. Cir. 1986).

In response to applicant's argument that there is no suggestion to combine the references, the examiner recognizes that obviousness can only be established by combining or modifying the teachings of the prior art to produce the claimed invention where there is some teaching, suggestion, or motivation to do so found either in the references themselves or in the knowledge generally available to one of ordinary skill in the art. See *In re Fine*, 837 F.2d 1071, 5 USPQ2d 1596 (Fed. Cir. 1988) and *In re*

Jones, 958 F.2d 347, 21 USPQ2d 1941 (Fed. Cir. 1992). In this case, reasoning has been provided in the statement of the rejection in the office action mailed 04/17/2008. It is noted that Ohmi (col. 3, lines 58-62 and col. 4, lines 4-7) clearly discloses a good reason why one skilled in the art would like to replace a conventional thermal silicon oxide film of Fujii with the silicon oxide film containing a rare gas disclosed by Ohmi.

Page 9

In response to applicant's argument that reason to combine references is not the same as applicant's, if it is obvious to combine references for one reason it is obvious to combine references for all reasons. In re Graf, 145 USPQ 197 (CCPA 1965); In re Finsterwalder, 168 USPQ 530 (USPQ 1970); In re Kronig, 539 F.2d 1300, 190 USPQ 425 (CCPA 1976). In re Dillon, 892 F.2d 1544, 13 USPQ 1337 (1989); In re Dillon 919 F.2d 688, 16 USPQ 1897 Fed. Cir. 1990.

In response to applicant's argument that the present inventors recognize a difference between silicon and SiC and degradation of the properties of the insulating film, the fact that applicant has recognized another advantage which would flow naturally from following the suggestion of the prior art cannot be the basis for patentability when the differences would otherwise be obvious. See *Ex parte Obiaya*, 227 USPQ 58, 60 (Bd. Pat. App. & Inter. 1985).

In response to applicant's argument that neither of these prior art references recognize the problem solved by the present invention, it has been held that the mere fact that the references fail to evince an appreciation of the problem identified and solved by applicant is not, standing alone, conclusive evidence of the nonobviousness of the claimed subject matter. The reference may suggest doing what applicant has

done even though workers in the art were ignorant of the existence of the problem. In re Gershon, 152 USPQ 602 (CCPA 1967). Furthermore, it not necessary that the prior art suggest the combination to achieve the same advantage or result discovered by applicant. In re Linter, 458 F.2d 1013, 173 USPQ 560 (CCPA 1972); in re Dillon, 919 F.2d 688, 16 USPQ2d 1897 (Fed. Cir. 1990), cert. Denied, 500 U.S. 904 (1991).

Conclusion

THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the mailing date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Thien F. Tran whose telephone number is (571) 272-1665. The examiner can normally be reached on 7:30AM - 4:00PM Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Drew N. Richards can be reached on (571) 272-1736. The fax phone

Application/Control Number: 10/553,416 Page 11

Art Unit: 2895

number for the organization where this application or proceeding is assigned is 571-

273-8300.

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system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

Thien F Tran
Primary Examiner
Art Unit 2895

/Thien F Tran/ Primary Examiner, Art Unit 2895